S8050

General Purpose Transistors
NPN Silicon

FEATURES

Complimentary to S8550

MARKING: J3Y

SOT-23

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

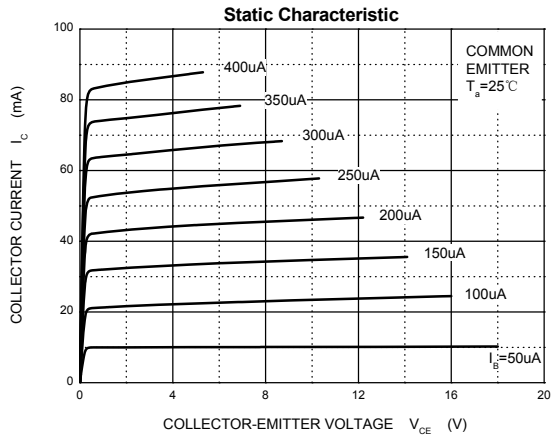
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	500	mA
P_C	Collector Power Dissipation	300	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	417	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55～+150	℃

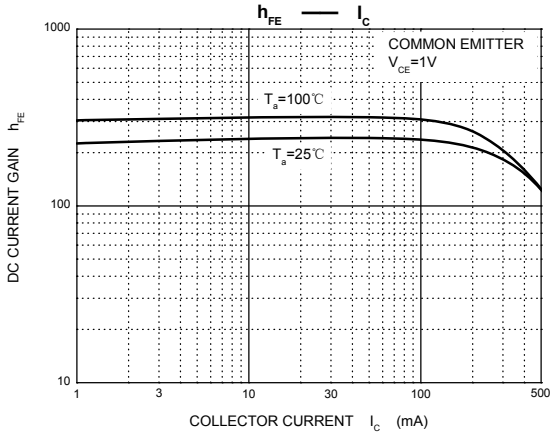
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

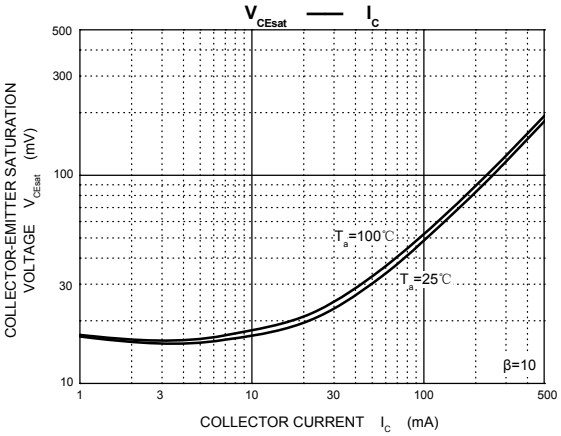
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40 V , I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CB}=20V , I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V , I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C= 50mA	120		400	
	$h_{FE(2)}$	V_{CE}=1V, I_C= 500mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500 mA, I_B= 50mA			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=500 mA, I_B= 50mA			1.2	V
Transition frequency	f_T	V_{CE}=6V, I_C= 20mA f=30MHz	150			MHz

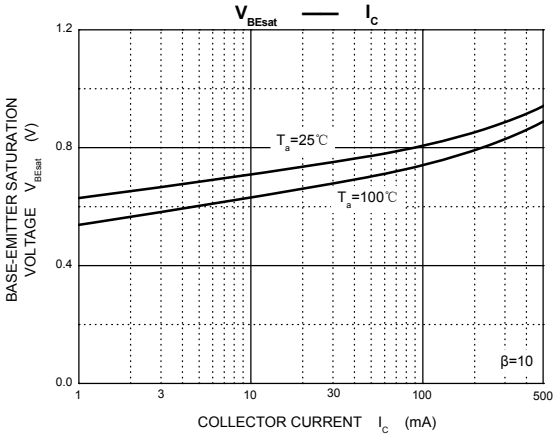
CLASSIFICATION OF $h_{FE(1)}$

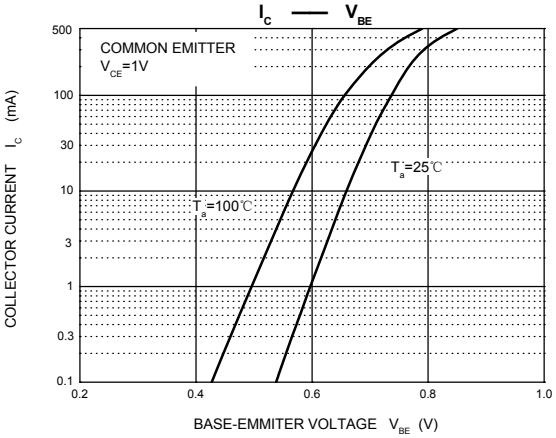
Rank	L	H	J
Range	120-200	200-350	300-400

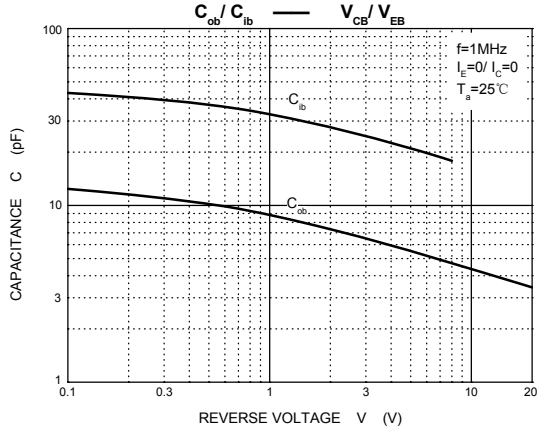

Static Characteristic
COMMON EMITTER
T_a=25℃
400uA
350uA
300uA
250uA
200uA
150uA
100uA
I_B=50uA
COLLECTOR CURRENT I_C (mA)
COLLECTOR-EMITTER VOLTAGE V_{CE} (V)

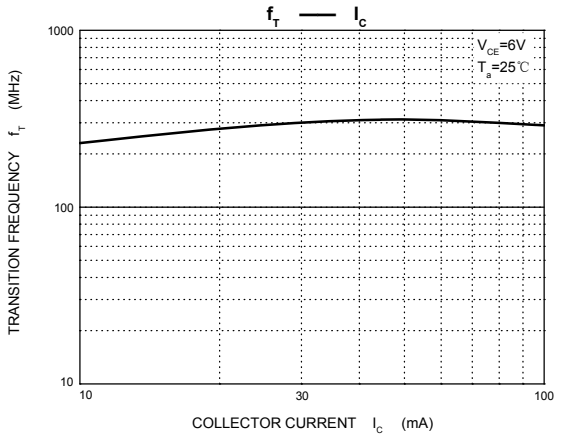

h_{FE} —— I_C
COMMON EMITTER
V_{CE}=1V
T_a=100℃
T_a=25℃
DC CURRENT GAIN h_{FE}
COLLECTOR CURRENT I_C (mA)

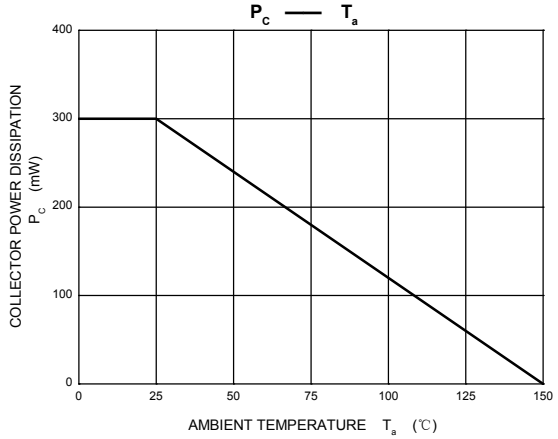

V_{CEsat} —— I_C
T_a=100℃
T_a=25℃
β=10
COLLECTOR-EMITTER SATURATION VOLTAGE V_{CEsat} (mV)
COLLECTOR CURRENT I_C (mA)


V_{BEsat} —— I_C
T_a=25℃
T_a=100℃
β=10
BASE-EMITTER SATURATION VOLTAGE V_{BEsat} (V)
COLLECTOR CURRENT I_C (mA)

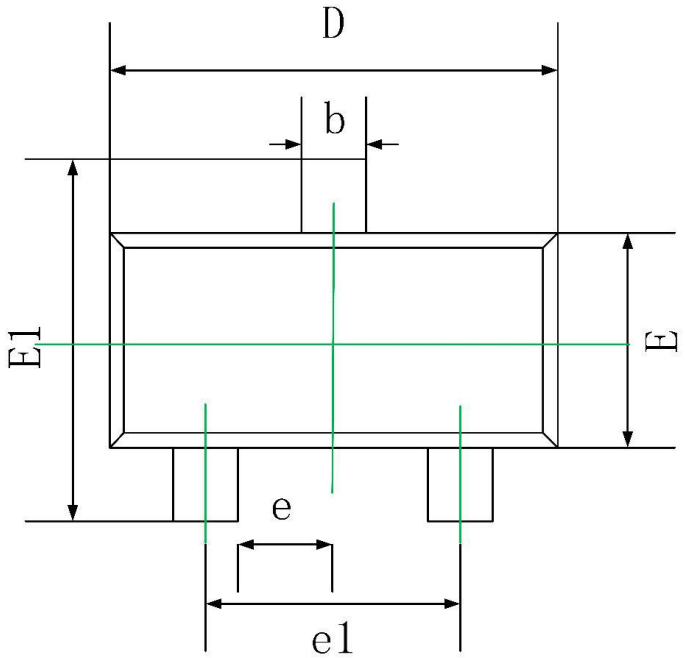

I_C —— V_{BE}
COMMON EMITTER
V_{CE}=1V
T_a=25℃
T_a=100℃
COLLECTOR CURRENT I_C (mA)
BASE-EMMITER VOLTAGE V_{BE} (V)

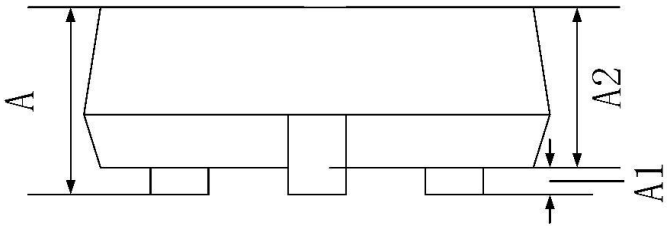

C_{ob}/ C_{ib} —— V_{CB}/ V_{EB}
f=1MHz
I_E=0/ I_C=0
T_a=25℃
C_{ib}
C_{ob}
CAPACITANCE C (pF)
REVERSE VOLTAGE V (V)

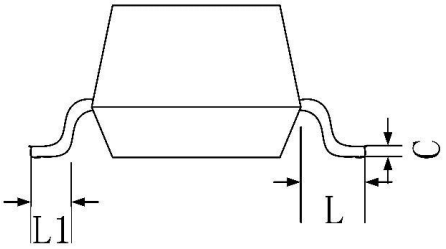

f_T —— I_C
V_{CE}=6V
T_a=25℃
TRANSITION FREQUENCY f_T (MHz)
COLLECTOR CURRENT I_C (mA)


P_C —— T_a
COLLECTOR POWER DISSIPATION P_C (mW)
AMBIENT TEMPERATURE T_a (℃)

SOT-23 Package Information

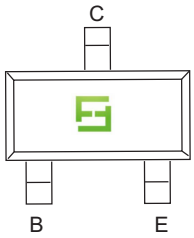
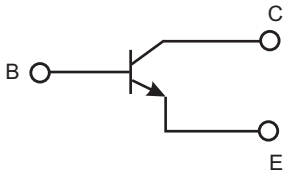






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020

Pinning information

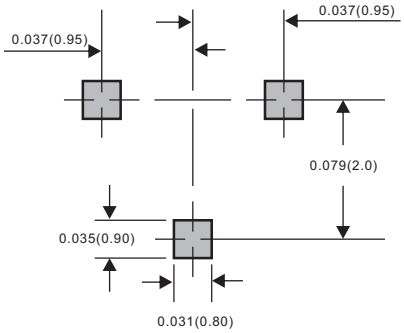
Pin	Simplified outline	Symbol
PinB Base PinC Collector PinE Emitter		

Marking

Type number	Marking code
S8050	J3Y

Suggested solder pad layout

SOT-23



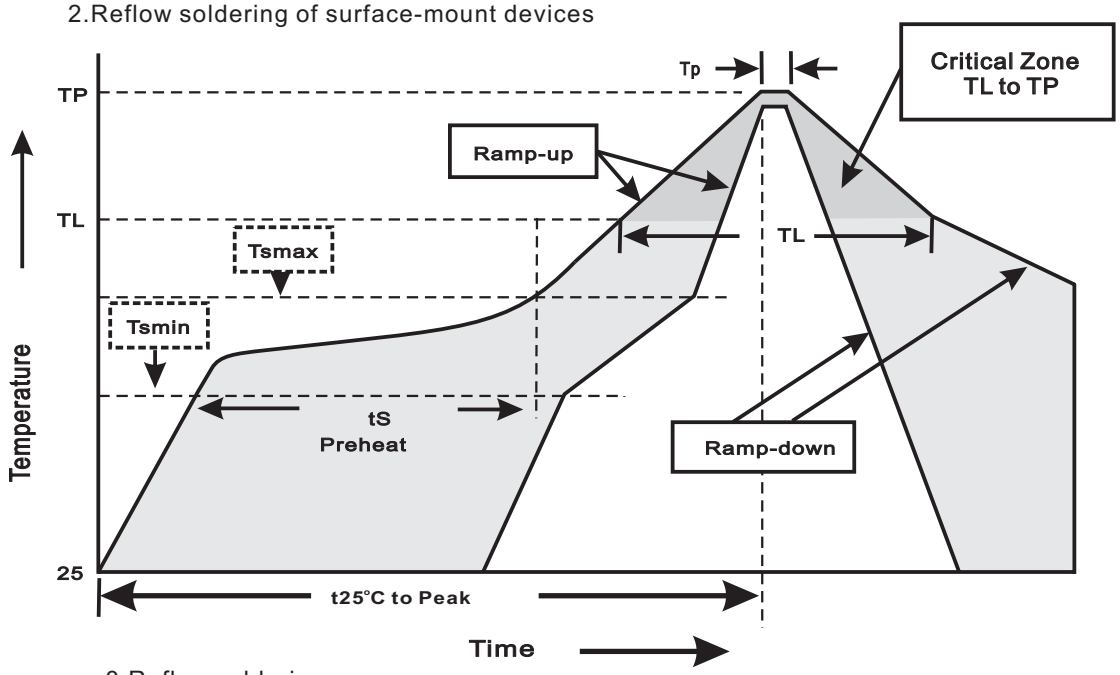
Dimensions in inches and (millimeters)

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-23	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	11.6

Suggested thermal profiles for soldering processes

1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T_L to T_P)	<3°C/sec
Preheat -Temperature Min(Tsmin) -Temperature Max(Tsmax) -Time(min to max)(t_s)	 150°C 200°C 60~120sec
Tsmax to T_L -Ramp-upRate	 <3°C/sec
Time maintained above: -Temperature(T_L) -Time(t_L)	 217°C 60~260sec
Peak Temperature(T_P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t_P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes